

Study of irradiated NinN production and LGAD doping profiles

Tuesday 23 June 2015 10:00 (20 minutes)

Trough SiMS measurements, the evolution of the doping profile is been studied for irradiated NinN samples at fluences of 10^{15} neq/cm², while the transient current technique is used on diodes of the same implantation profile n order to evaluate the electrical characteristics evolution as a function of the received dose. Comparison and conclusions are established with the non-irradiated case both for the profile evolution and the intrinsic characteristics of the samples. A SiMS vs process simulation approach is used to model and control the new LGAD production in an attempt to understand post irradiation behavior and electrical characteristic.

Author: GKOU GKOUSIS, Vagelis (Laboratoire de l'Accelérateur Lineaire (FR))

Co-authors: LOUNIS, Abdenour (Laboratoire de l'Accelérateur Lineaire (FR)); NELLIST, Clara (LAL-Orsay (FR))

Presenter: GKOU GKOUSIS, Vagelis (Laboratoire de l'Accelérateur Lineaire (FR))

Session Classification: LGAD